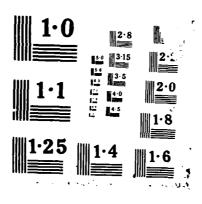
A PRACTICAL INTERFEROMETRIC TECHNIQUE FOR MASK/MAFER ALIGNMENT DURING PROXIMITY PRINTING(U) MAYAL OCEAN SYSTEMS CENTER SAN DIEGO CA J L BARTELT ET AL. MAY 87 F/G 9/1 AD-A191 895 1/1 UNCLASSIFIED



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J. L. Bartelt and R. D. Olney Hughes Research Laboratories + 3011 Malibu Canyon Road Malibu, CA 90265

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